

**100V N-CHANNEL ENHANCEMENT MODE MOSFET**

**MAIN CHARACTERISTICS**

|                               |                             |
|-------------------------------|-----------------------------|
| $I_D$                         | 5A                          |
| $V_{DS}$                      | 100V                        |
| $R_{DS(on)-typ}(@V_{GS}=10V)$ | $< 138m\Omega$ (Typ: 108mΩ) |

**FEATURES**

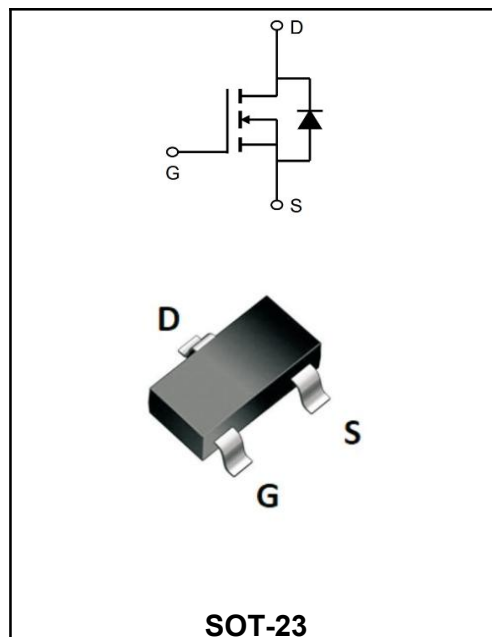
- ◆ Low  $R_{DS(on)}$  & FOM
- ◆ Extremely low switching loss.
- ◆ Excellent stability and uniformity.
- ◆ Fast switching and soft recovery

**APPLICATION**

- ◆ Consumer electronic power supply
- ◆ Motor control
- ◆ Synchronous-rectification
- ◆ Isolated DC/DC convertor

**MECHANICAL DATA**

- ◆ Case: SOT-23
- ◆ Epoxy UL: 94V-0
- ◆ Mounting Position: Any



**Marking Code**

|                 |             |
|-----------------|-------------|
| <b>YFW5N10B</b> | <b>5N10</b> |
|-----------------|-------------|

**Maximum Ratings at  $T_c=25^{\circ}C$  unless otherwise specified**

| Characteristics                                | Symbols         | Value       | Units         |
|------------------------------------------------|-----------------|-------------|---------------|
| Drain-Source Voltage                           | $V_{DS}$        | 100         | V             |
| Gate - Source Voltage                          | $V_{GS}$        | $\pm 20$    | V             |
| Continuous Drain Current                       | $I_D$           | 5           | A             |
| Pulsed Drain Current (note1)                   | $I_{DM}$        | 15          | A             |
| Maximum Power Dissipation                      | $P_D$           | 400         | mW            |
| Operating Temperature Range                    | $T_J$           | 150         | $^{\circ}C$   |
| Storage Temperature Range                      | $T_{STG}$       | -50 to +150 | $^{\circ}C$   |
| Thermal Resistance, Junction to Ambient(note2) | $R_{\theta JA}$ | 85          | $^{\circ}C/W$ |

**Maximum Ratings at Tc=25°C unless otherwise specified**

| Characteristics                         | Test Condition                                              | Symbols      | Min | Typ  | Max       | Units      |
|-----------------------------------------|-------------------------------------------------------------|--------------|-----|------|-----------|------------|
| Drain-Source Breakdown Voltage          | $V_{GS}=0V, I_D=250\mu A$                                   | $BV_{DSS}$   | 100 | -    | -         | V          |
| Gate-Body Leakage Current               | $V_{GS}=\pm 20V, V_{DS}=0V$                                 | $I_{GSS}$    | -   | -    | $\pm 100$ | nA         |
| Zero Gate Voltage Drain Current         | $V_{DS}=100V, V_{GS}=0V$                                    | $I_{DSS}$    | -   | -    | 1         | $\mu A$    |
| Gate -Threshold Voltage(note3)          | $V_{DS}=V_{GS}, I_D=250\mu A$                               | $V_{GS(th)}$ | 1.0 | 1.6  | 2.5       | V          |
| Drain-Source On-State Resistance(note3) | $V_{GS}=10V, I_D=3A$                                        | $R_{DS(ON)}$ | -   | 108  | 138       | m $\Omega$ |
|                                         | $V_{GS}=4.5V, I_D=2A$                                       |              | -   | 130  | 185       |            |
| Input Capacitance                       | $V_{DS}=50V$<br>$V_{GS}=0V$<br>$f=1.0MHz$                   | $C_{iss}$    | -   | 200  | -         | pF         |
| Output Capacitance                      |                                                             | $C_{oss}$    | -   | 30   | -         |            |
| Reverse Transfer Capacitance            |                                                             | $C_{rss}$    | -   | 2    | -         |            |
| Turn-on delay time                      | $V_{DD}=50V$<br>$V_{GS}=10V$<br>$I_D=3A$<br>$R_G=2.0\Omega$ | $t_{d(on)}$  | -   | 12.5 | -         | ns         |
| Turn-on Rise Time                       |                                                             | $T_r$        | -   | 19.3 | -         |            |
| Turn-Off Delay Time                     |                                                             | $t_{d(OFF)}$ | -   | 20   | -         |            |
| Turn-Off Fall Time                      |                                                             | $t_f$        | -   | 28   | -         |            |
| Total Gate Charge                       | $V_{DS}=50V,$<br>$V_{GS}=10V,$<br>$I_D=3A$                  | $Q_g$        | -   | 4    | -         | nC         |
| Gate-Source Charge                      |                                                             | $Q_{gs}$     | -   | 0.5  | -         |            |
| Gate-Drain Charge                       |                                                             | $Q_{gd}$     | -   | 1.4  | -         |            |
| Body Diode Voltage(note3)               | $I_S=3A, V_{GS}=0V$                                         | $V_{SD}$     | -   | -    | 1.2       | V          |

Notes:

1. Repetitive rating : Pulse width limited by junction temperature.
2. Surface mounted on FR4 board,  $t \leq 10s$
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to producing.

Typical Characteristics

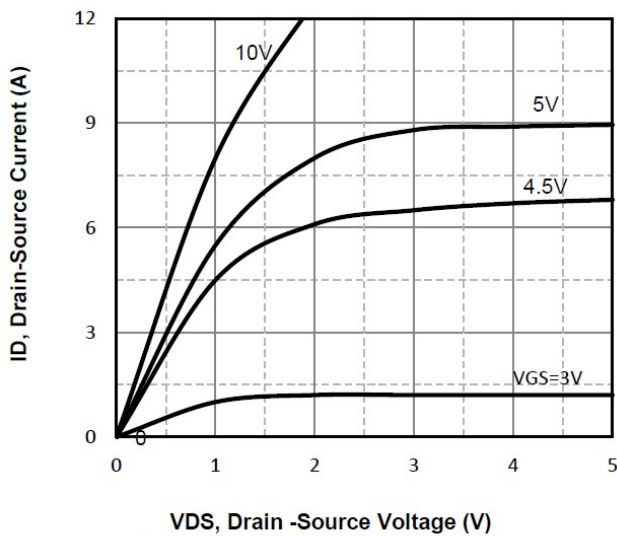


Fig1. Typical Output Characteristics

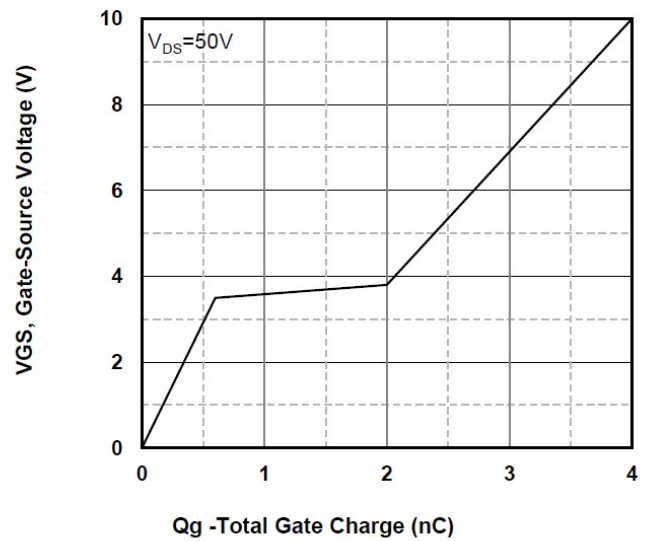


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

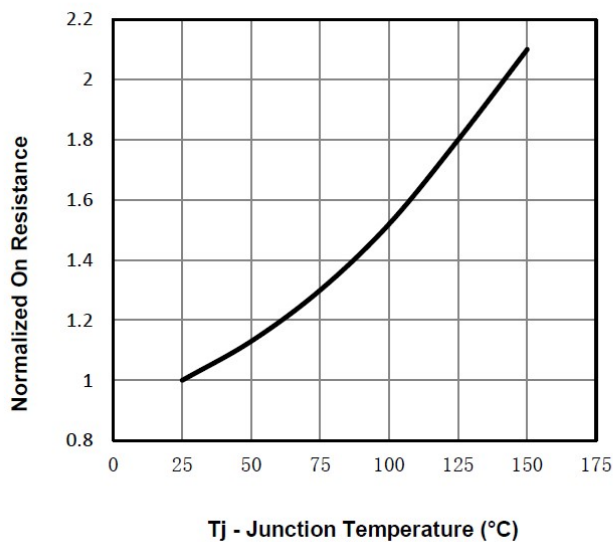


Fig3. Normalized On-Resistance Vs. Temperature

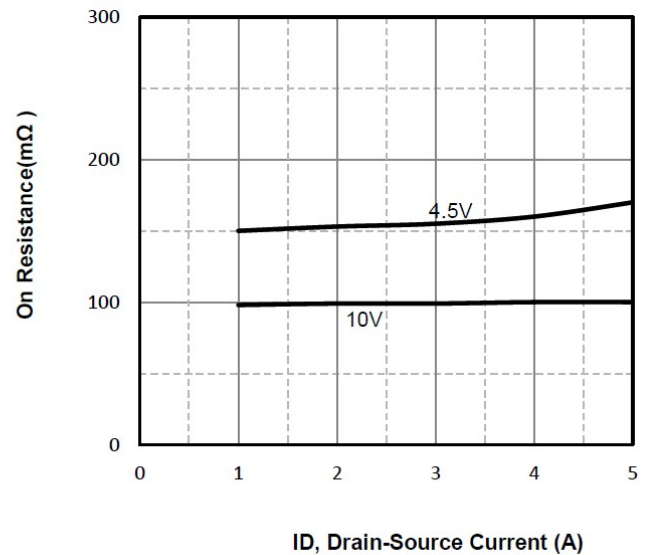


Fig4. On-Resistance Vs. Drain-Source Current

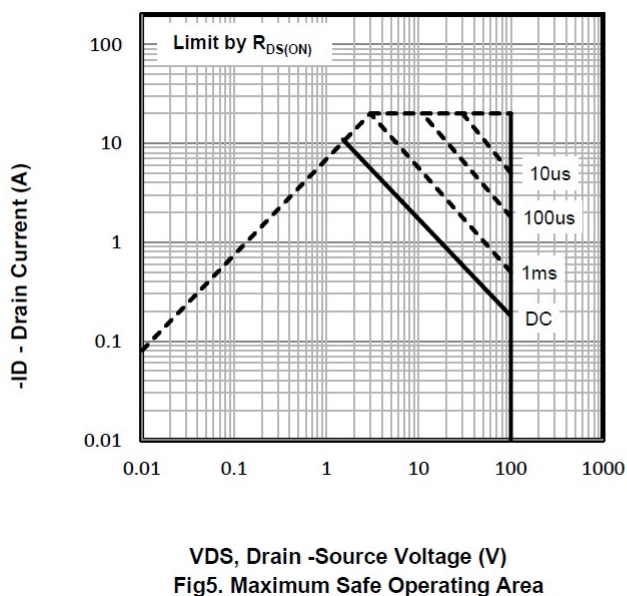


Fig5. Maximum Safe Operating Area

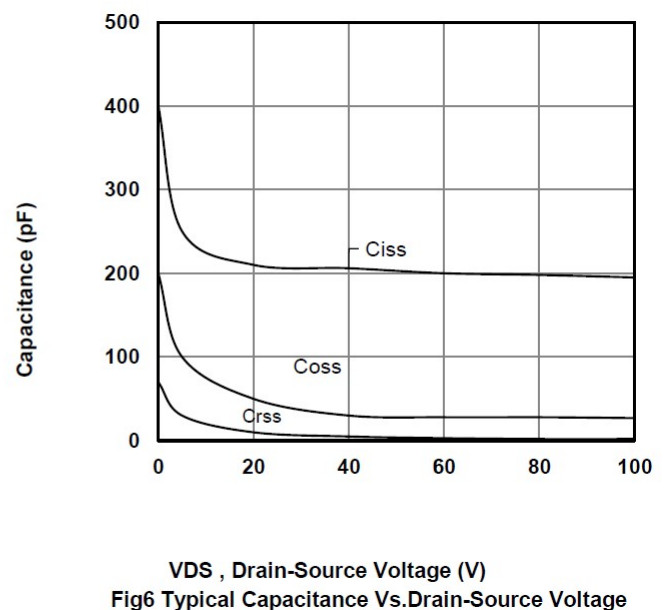


Fig6. Typical Capacitance Vs. Drain-Source Voltage

### Ordering information

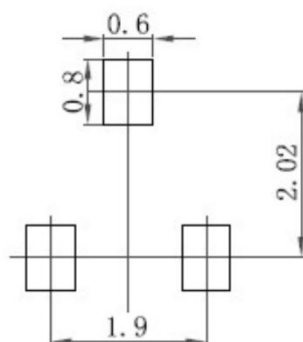
| Package | Packing Description | Base Quantity | Packing Quantity              |
|---------|---------------------|---------------|-------------------------------|
| SOT-23  | Tape/Reel, 7" reel  | 3000pcs/Reel  | 24000PCS/Box 120000PCS/Carton |

### Package Dimensions

#### SOT-23

| Dim. | Millimeter (mm) |      | mil  |      |
|------|-----------------|------|------|------|
|      | Min.            | Max. | Min. | Max. |
| A    | 0.9             | 1.15 | 35   | 45   |
| A1   | 0.1             |      | 3.9  |      |
| bp   | 0.38            | 0.48 | 15   | 19   |
| C    | 0.09            | 0.15 | 3.54 | 5.9  |
| D    | 2.8             | 3.0  | 110  | 118  |
| E    | 1.2             | 1.4  | 47   | 55   |
| e    | 1.9             |      | 75   |      |
| e1   | 0.95            |      | 37   |      |
| HE   | 2.1             | 2.55 | 83   | 100  |
| Lp   | 0.15            | 0.45 | 5.9  | 18   |
| Q    | 0.45            | 0.55 | 18   | 22   |
| v    | 0.2             |      | 7.9  |      |
| W    | 0.1             |      | 4    |      |

### The recommended mounting pad size



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